## 现代电子显微学进展及其在材料科学中的应用,

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## Advanced transmission electron microscopy and its applications in material sciences

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**Abstract:** Recent progresses in the fields of high-resolution electron microscopy (Cs-TEM), electron energy loss spectroscopy and electron holography have been briefly reviewed. It is emphasized that numerous significant structural issues in material science could be well addressed. For instance, charge ordering and oxygen deficiency in functional oxides, magnetic tunnel junctions with MgO-barrier and the manganite-based heterojunctions. My talk will also focus on some experimental results on interfacial structural features and oxygen diffusion in SrTiO<sub>3</sub>/Si films related heterojunctions. High-resolution TEM investigations the La<sub>0.9</sub>Sr<sub>0.1</sub>MnO<sub>3</sub>/SrTiO<sub>3</sub>/Si heterojunctions suggested that the thickness of the SiOx interfacial layer change visibly from one sample to another grown under slightly different conditions. The electron-energy loss spectroscopy analyses on the LSMO/STO/Si interfacial region indicated that the Si ions are in intermediate oxidation states in the amorphous layer. Electron holography measurements revealed that notable negative charges accumulate in the amorphous SiO<sub>x</sub> layer, the energy barrier between the Si substrate and the LSMO film have been estimated based on experimental data.

## References:

- C. Ma, H. X. Yang, H. F. Tian, H. L Shi, J. B. Lu, Z. W. Wang, L. J. Zeng, G. F. Chen, N. L. Wang, and J. Q. Li\*, Physical Review B (R) ) 79 (2009) 060506.
- 2. H.Y Liang, H.X. Xu, J. Q.Li, **J. Am. Chem. Soc.** 131(2009)6068.
- L. J. Zeng, C. Ma, H. X. Yang, R. J. Xiao, and J. Q. Li\*, Physical Review B 77 (2008) 024107.
- 4. Y. Zhang, H. X. Yang, C. Ma, H. F. Tian & J. Q. Li \* Phys. Rev. Lett. 98 (2007) 247602.
- Z. A. Li, H. X. Yang, H. F. Tian, J. Q. Li\*, J. R. Cheng, J. G. Chen, *Appl. Phys. Lett.* 90 (2007)182904.